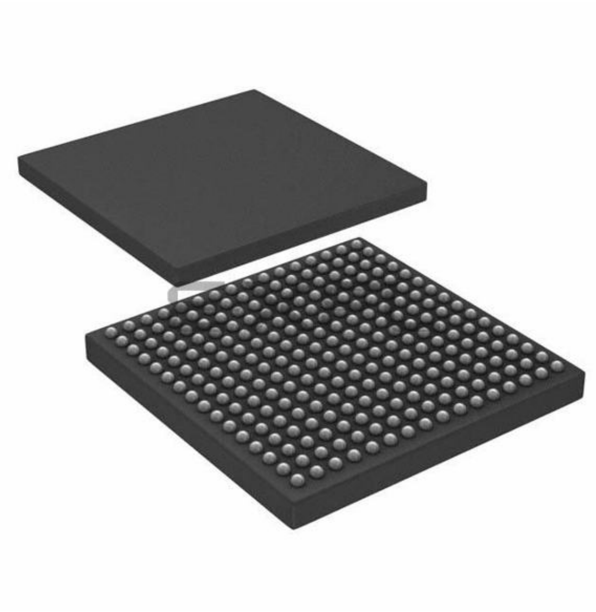
Microchip Technology - A3PE600-FG256I Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	165
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe600-fg256i

Table 2-8 • **Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings (continued)**

	VMV (V)	Static Power PDC2 (mW)[1]	Dynamic Power PAC9 (µW/MHz)[2]
HSTL (I)	1.5	0.17	2.03
HSTL (II)	1.5	0.17	2.03
SSTL2 (I)	2.5	1.38	4.48
SSTL2 (II)	2.5	1.38	4.48
SSTL3 (I)	3.3	3.21	9.26
SSTL3 (II)	3.3	3.21	9.26
Differential			
LVDS/B-LVDS/M-LVDS	2.5	2.26	1.50
LVPECL	3.3	5.71	2.17

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.*

Table 2-9 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings** [1]

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL/LVCMOS	35	3.3	–	474.70
3.3 V LVTTL/LVCMOS Wide Range[4]	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-11 on page 2-11.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-12 on page 2-11.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-12 on page 2-11. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-11 on page 2-11.

F_{CLK} is the global clock signal frequency.

User I/O Characteristics

Timing Model

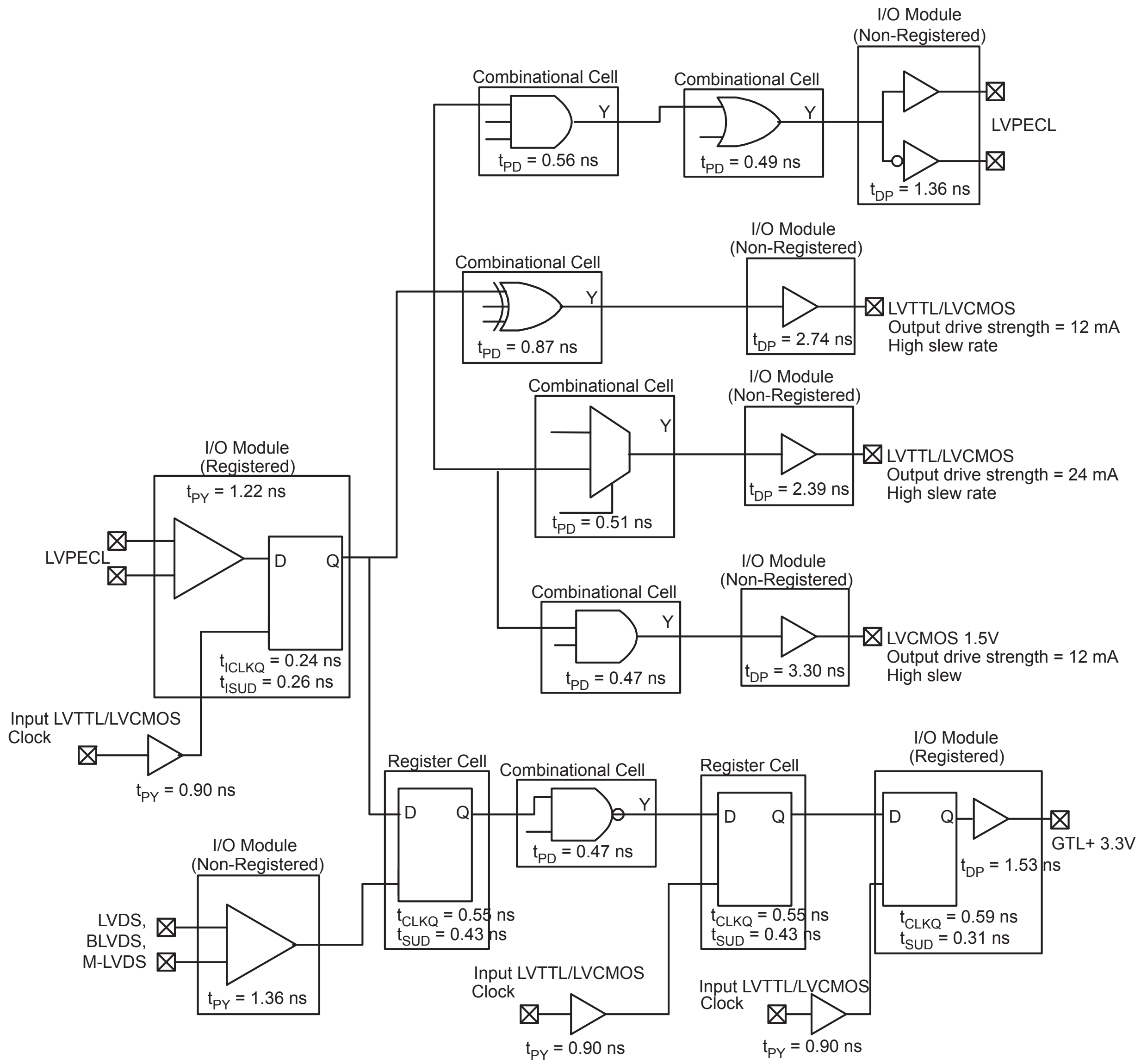


Figure 2-2 • **Timing Model**
Operating Conditions: –2 Speed, Commercial Temperature Range (T_J = 70°C), Worst-Case VCC = 1.425 V

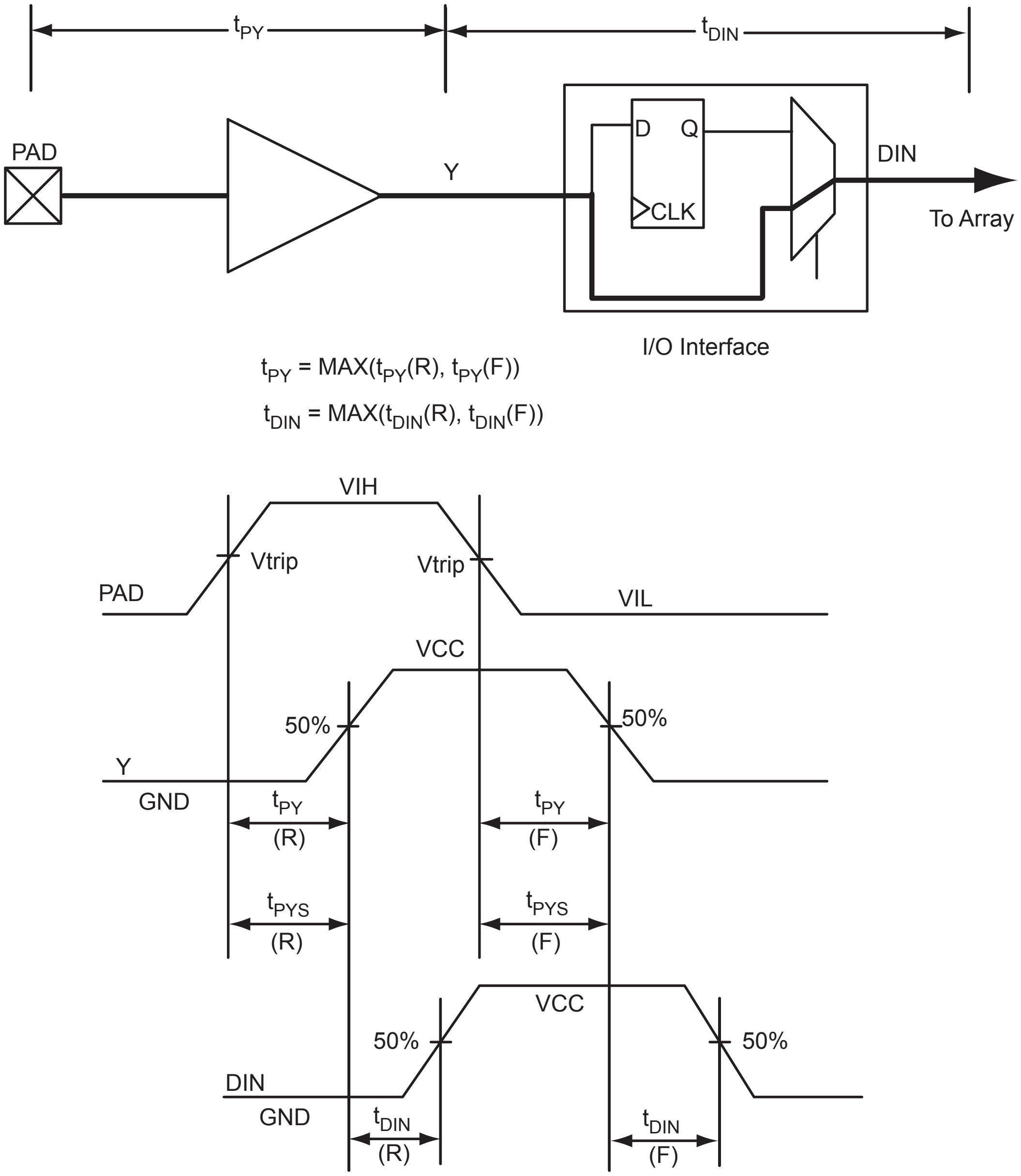


Figure 2-3 • **Input Buffer Timing Model and Delays (example)**

***Table 2-14* • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions**

	Commercial[1]		**Industrial[2]**	
	IIL[3]	**IIH[4]**	**IIL[3]**	**IIH[4]**
DC I/O Standards	**µA**	**µA**	**µA**	**µA**
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15
3.3 V GTL	10	10	15	15
2.5 V GTL	10	10	15	15
3.3 V GTL+	10	10	15	15
2.5 V GTL+	10	10	15	15
HSTL (I)	10	10	15	15
HSTL (II)	10	10	15	15
SSTL2 (I)	10	10	15	15
SSTL2 (II)	10	10	15	15
SSTL3 (I)	10	10	15	15
SSTL3 (II)	10	10	15	15

Notes:

1. *Commercial range (0°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
4. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*

Table 2-17 • **Summary of I/O Timing Characteristics—Software Default Settings**
–2 Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option)[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)
3.3 V LVTTL / 3.3 V LVCMOS	12	12	High	35	–	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	35	–	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79
2.5 V LVCMOS	12	12	High	35	–	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28
1.8 V LVCMOS	12	12	High	35	–	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98
1.5 V LVCMOS	12	12	High	35	–	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37
3.3 V PCI	Per PCI spec	–	High	10	25[3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[3]	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V GTL	20[4]	–	High	10	25	0.45	1.55	0.03	2.19	–	0.32	1.52	1.55	–	–	3.19	3.22
2.5 V GTL	20[4]	–	High	10	25	0.45	1.59	0.03	1.83	–	0.32	1.61	1.59	–	–	3.28	3.26
3.3 V GTL+	35	–	High	10	25	0.45	1.53	0.03	1.19	–	0.32	1.56	1.53	–	–	3.23	3.20
2.5 V GTL+	33	–	High	10	25	0.45	1.65	0.03	1.13	–	0.32	1.68	1.57	–	–	3.35	3.24
HSTL (I)	8	–	High	20	50	0.49	2.37	0.03	1.59	–	0.32	2.42	2.35	–	–	4.09	4.02
HSTL (II)	15[4]	–	High	20	25	0.49	2.26	0.03	1.59	–	0.32	2.30	2.03	–	–	3.97	3.70
SSTL2 (I)	15	–	High	30	50	0.49	1.59	0.03	1.00	–	0.32	1.62	1.38	–	–	3.29	3.05
SSTL2 (II)	18	–	High	30	25	0.49	1.62	0.03	1.00	–	0.32	1.65	1.32	–	–	3.32	2.99
SSTL3 (I)	14	–	High	30	50	0.49	1.72	0.03	0.93	–	0.32	1.75	1.37	–	–	3.42	3.04
SSTL3 (II)	21	–	High	30	25	0.49	1.54	0.03	0.93	–	0.32	1.57	1.25	–	–	3.24	2.92
LVDS/B-LVDS/ M-LVDS	24	–	High	–	–	0.49	1.40	0.03	1.36	–	–	–	–	–	–	–	–
LVPECL	24	–	High	–	–	0.49	1.36	0.03	1.22	–	–	–	–	–	–	–	–

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3V wide range as specified in the JESD8b specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-38 for connectivity. This resistor is not required during normal operation.*
4. *Output drive strength is below JEDEC specification.*
5. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5.*

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer. The 3.3 V LVCMOS standard is supported as part of the 3.3 V LVTTL support.

***Table 2-25* • Minimum and Maximum DC Input and Output Levels**

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min., V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**µA[4]**	**µA[4]**
2 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

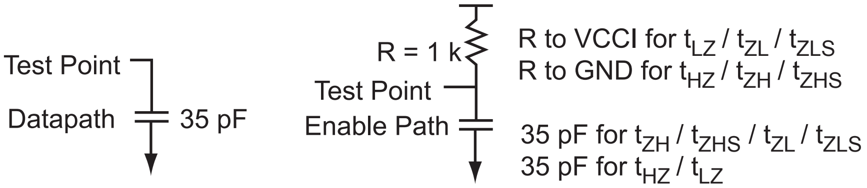


***Figure 2-6* • AC Loading**

***Table 2-26* • 3.3 V LVTTL / 3.3 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	1.4	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Table 2-36 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	12.00	0.04	1.51	1.66	0.43	12.23	11.61	2.72	2.20	14.46	13.85	ns
	–1	0.56	10.21	0.04	1.29	1.41	0.36	10.40	9.88	2.31	1.87	12.30	11.78	ns
	–2	0.49	8.96	0.03	1.13	1.24	0.32	9.13	8.67	2.03	1.64	10.80	10.34	ns
8 mA	Std.	0.66	8.73	0.04	1.51	1.66	0.43	8.89	8.01	3.10	2.93	11.13	10.25	ns
	–1	0.56	7.43	0.04	1.29	1.41	0.36	7.57	6.82	2.64	2.49	9.47	8.72	ns
	–2	0.49	6.52	0.03	1.13	1.24	0.32	6.64	5.98	2.32	2.19	8.31	7.65	ns
12 mA	Std.	0.66	6.77	0.04	1.51	1.66	0.43	6.90	6.11	3.37	3.39	9.14	8.34	ns
	–1	0.56	5.76	0.04	1.29	1.41	0.36	5.87	5.20	2.86	2.89	7.77	7.10	ns
	–2	0.49	5.06	0.03	1.13	1.24	0.32	5.15	4.56	2.51	2.53	6.82	6.23	ns
16 mA	Std.	0.66	6.31	0.04	1.51	1.66	0.43	6.42	5.73	3.42	3.52	8.66	7.96	ns
	–1	0.56	5.37	0.04	1.29	1.41	0.36	5.46	4.87	2.91	3.00	7.37	6.77	ns
	–2	0.49	4.71	0.03	1.13	1.24	0.32	4.80	4.28	2.56	2.63	6.47	5.95	ns
24 mA	Std.	0.66	5.93	0.04	1.51	1.66	0.43	6.04	5.70	3.49	4.00	8.28	7.94	ns
	–1	0.56	5.05	0.04	1.29	1.41	0.36	5.14	4.85	2.97	3.40	7.04	6.75	ns
	–2	0.49	4.43	0.03	1.13	1.24	0.32	4.51	4.26	2.61	2.99	6.18	5.93	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

***Table 2-41* • Minimum and Maximum DC Input and Output Levels**

1.5 V LVCMOS	**VIL**		**VIH**		**VOL**	**VOH**	**IOL**	**IOH**	**IOSL**	**IOSH**	**IIL[1]**	**IIH[2]**
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**μA[4]**	**μA[4]**
2 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10
6 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	6	6	39	32	10	10
8 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	8	8	55	66	10	10
12 mA	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12	55	66	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

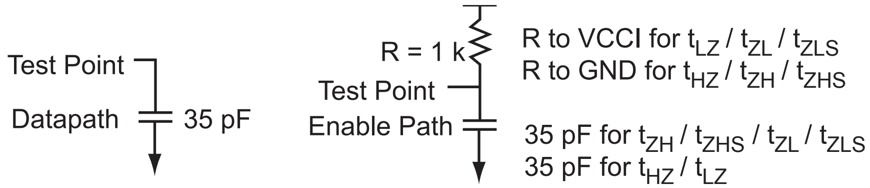


***Figure 2-10* • AC Loading**

***Table 2-42* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	**Input High (V)**	**Measuring Point* (V)**	**VREF (typ.) (V)**	**C_{LOAD} (pF)**
0	1.5	0.75	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Voltage-Referenced I/O Characteristics

3.3 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

***Table 2-48* • Minimum and Maximum DC Input and Output Levels**

3.3 V GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	181	268	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

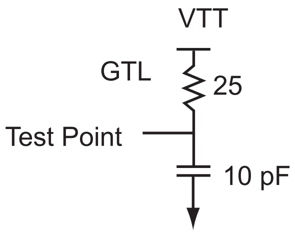


***Figure 2-12* • AC Loading**

***Table 2-49* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

***Table 2-50* • 3.3 V GTL**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.08	0.04	2.93	0.43	2.04	2.08			4.27	4.31	ns
–1	0.51	1.77	0.04	2.50	0.36	1.73	1.77			3.63	3.67	ns
–2	0.45	1.55	0.03	2.19	0.32	1.52	1.55			3.19	3.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-25 on page 2-53 for more information.

Table 2-85 **• Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-26 on page 2-55 for more information.*

Global Resource Characteristics

A3PE600 Clock Tree Topology

Clock delays are device-specific. Figure 2-38 is an example of a global tree used for clock routing. The global tree presented in Figure 2-38 is driven by a CCC located on the west side of the A3PE600 device. It is used to drive all D-flip-flops in the device.

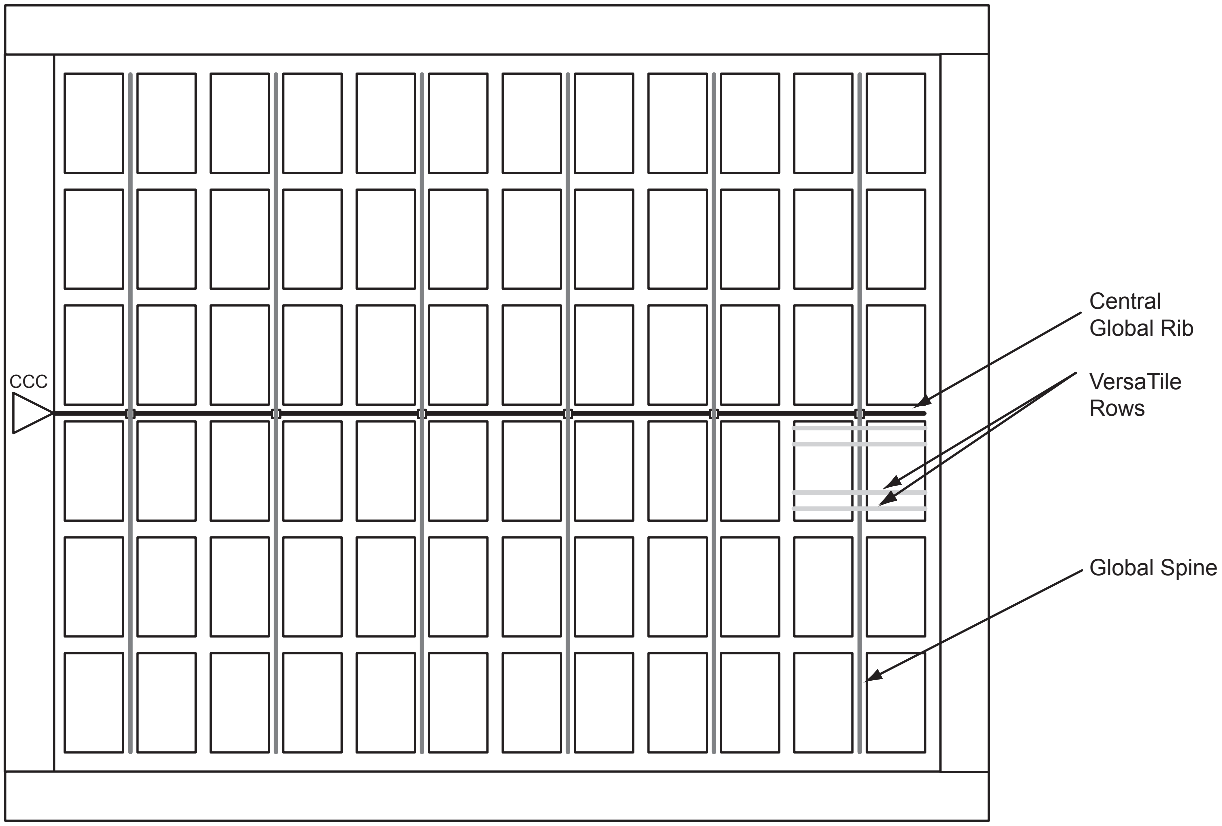
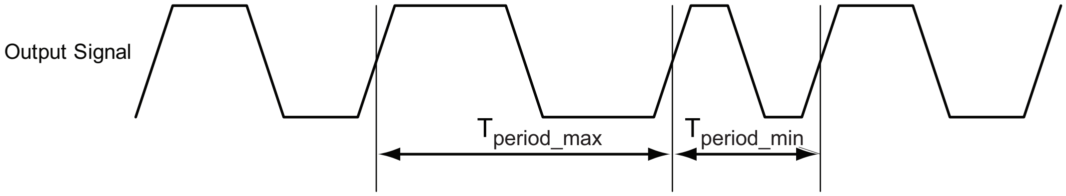


Figure 2-38 • **Example of Global Tree Use in an A3PE600 Device for Clock Routing**

Global Tree Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are I/O standard–dependent, and the clock may be driven and conditioned internally by the CCC module. For more details on clock conditioning capabilities, refer to the "Clock Conditioning Circuits" section on page 2-70. Table 2-95 on page 2-69, Table 2-96 on page 2-69, and Table 2-97 on page 2-69 present minimum and maximum global clock delays within the device. Minimum and maximum delays are measured with minimum and maximum loading.



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} – T_{period\_min}$.

Figure 2-39 **• Peak-to-Peak Jitter Definition**

Timing Waveforms

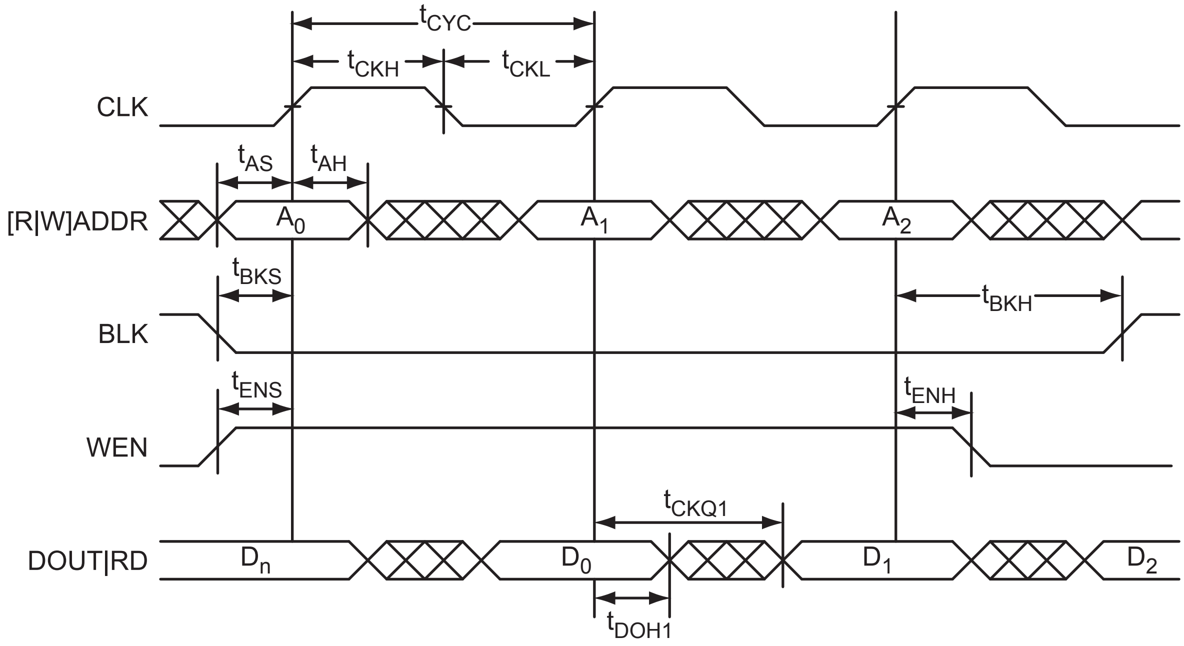


Figure 2-41 • **RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

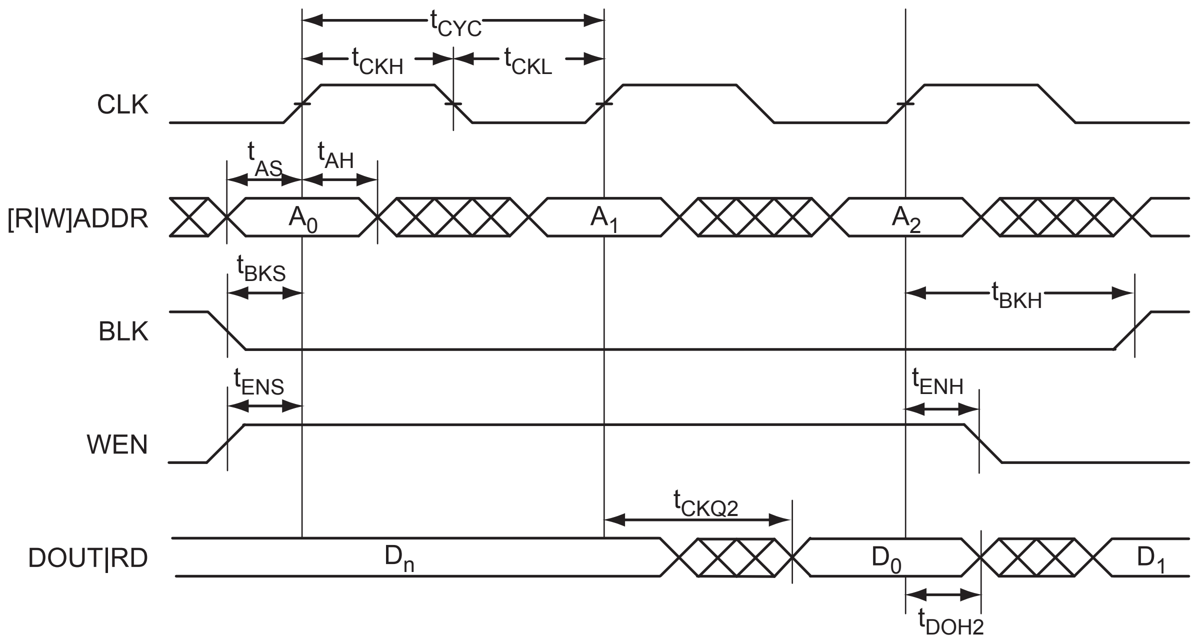


Figure 2-42 • **RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

4 – Package Pin Assignments

PQ208

Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG256	
Pin Number	**A3PE600 Function**
A1	GND
A2	GAA0/IO00NDB0V0
A3	GAA1/IO00PDB0V0
A4	GAB0/IO01NDB0V0
A5	IO05PDB0V0
A6	IO10PDB0V1
A7	IO12PDB0V2
A8	IO16NDB0V2
A9	IO23NDB1V0
A10	IO23PDB1V0
A11	IO28NDB1V1
A12	IO28PDB1V1
A13	GBB1/IO34PDB1V1
A14	GBA0/IO35NDB1V1
A15	GBA1/IO35PDB1V1
A16	GND
B1	GAB2/IO133PDB7V1
B2	GAA2/IO134PDB7V1
B3	GNDQ
B4	GAB1/IO01PDB0V0
B5	IO05NDB0V0
B6	IO10NDB0V1
B7	IO12NDB0V2
B8	IO16PDB0V2
B9	IO20NDB1V0
B10	IO24NDB1V0
B11	IO24PDB1V0
B12	GBC1/IO33PDB1V1
B13	GBB0/IO34NDB1V1
B14	GNDQ
B15	GBA2/IO36PDB2V0
B16	IO42NDB2V0
C1	IO133NDB7V1
C2	IO134NDB7V1
C3	VMV7
C4	VCCPLA
C5	GAC0/IO02NDB0V0
C6	GAC1/IO02PDB0V0
C7	IO15NDB0V2
C8	IO15PDB0V2
C9	IO20PDB1V0
C10	IO25NDB1V0
C11	IO27PDB1V0
C12	GBC0/IO33NDB1V1
C13	VCCPLB
C14	VMV2
C15	IO36NDB2V0
C16	IO42PDB2V0
D1	IO128PDB7V1
D2	IO129PDB7V1
D3	GAC2/IO132PDB7V1
D4	VCOMPLA
D5	GNDQ
D6	IO09NDB0V1
D7	IO09PDB0V1
D8	IO13PDB0V2
D9	IO21PDB1V0
D10	IO25PDB1V0
D11	IO27NDB1V0
D12	GNDQ
D13	VCOMPLB
D14	GBB2/IO37PDB2V0
D15	IO39PDB2V0
D16	IO39NDB2V0
E1	IO128NDB7V1
E2	IO129NDB7V1
E3	IO132NDB7V1
E4	IO130PDB7V1
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO13NDB0V2
E9	IO21NDB1V0
E10	VCCIB1
E11	VCCIB1
E12	VMV1
E13	GBC2/IO38PDB2V0
E14	IO37NDB2V0
E15	IO41NDB2V0
E16	IO41PDB2V0
F1	IO124PDB7V0
F2	IO125PDB7V0
F3	IO126PDB7V0
F4	IO130NDB7V1
F5	VCCIB7
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB2
F13	IO38NDB2V0
F14	IO40NDB2V0
F15	IO40PDB2V0
F16	IO45PSB2V1
G1	IO124NDB7V0
G2	IO125NDB7V0
G3	IO126NDB7V0
G4	GFC1/IO120PPB7V0
G5	VCCIB7
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB2

FG484	
Pin Number	**A3PE1500 Function**
H19	IO67PDB2V1
H20	VCC
H21	VMV2
H22	IO74PSB2V2
J1	IO212NDB7V2
J2	IO212PDB7V2
J3	VMV7
J4	IO206PDB7V1
J5	IO204PDB7V1
J6	IO210PDB7V2
J7	IO215NDB7V3
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO60NDB2V0
J17	IO65NDB2V1
J18	IO65PDB2V1
J19	IO75PPB2V2
J20	GNDQ
J21	IO77PDB2V2
J22	IO79PDB2V3
K1	IO200NDB7V1
K2	IO200PDB7V1
K3	GNDQ
K4	IO206NDB7V1
K5	IO204NDB7V1
K6	IO210NDB7V2
K7	GFC1/IO192PPB7V0
K8	VCCIB7
K9	VCC
K10	GND

FG484	
Pin Number	**A3PE1500 Function**
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB2
K16	GCC1/IO85PPB2V3
K17	IO73NDB2V2
K18	IO73PDB2V2
K19	IO81NPB2V3
K20	IO75NPB2V2
K21	IO77NDB2V2
K22	IO79NDB2V3
L1	NC
L2	IO196PDB7V0
L3	IO196NDB7V0
L4	GFB0/IO191NPB7V0
L5	GFA0/IO190NDB6V2
L6	GFB1/IO191PPB7V0
L7	VCOMPLF
L8	GFC0/IO192NPB7V0
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO85NPB2V3
L16	GCB1/IO86PPB2V3
L17	GCA0/IO87NPB3V0
L18	VCOMPLC
L19	GCB0/IO86NPB2V3
L20	IO81PPB2V3
L21	IO83NDB2V3
L22	IO83PDB2V3
M1	GNDQ
M2	IO185NPB6V2

FG484	
Pin Number	**A3PE1500 Function**
M3	IO189NDB6V2
M4	GFA2/IO189PDB6V2
M5	GFA1/IO190PDB6V2
M6	VCCPLF
M7	IO188NDB6V2
M8	GFB2/IO188PDB6V2
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO89PPB3V0
M16	GCA1/IO87PPB3V0
M17	GCC2/IO90PPB3V0
M18	VCCPLC
M19	GCA2/IO88PDB3V0
M20	IO88NDB3V0
M21	IO93PDB3V0
M22	NC
N1	IO185PPB6V2
N2	IO183NDB6V2
N3	VMV6
N4	GFC2/IO187PPB6V2
N5	IO184PPB6V2
N6	IO186PDB6V2
N7	IO186NDB6V2
N8	VCCIB6
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB3
N16	IO89NPB3V0

FG896	
Pin Number	A3PE3000 Function
T11	VCC
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	GND
T19	GND
T20	VCC
T21	VCCIB3
T22	IO109NPB2V3
T23	IO116NDB3V0
T24	IO118NDB3V0
T25	IO122NPB3V1
T26	GCA1/IO114PPB3V0
T27	GCB0/IO113NPB2V3
T28	GCA2/IO115PPB3V0
T29	VCCPLC
T30	IO121PDB3V0
U1	IO268PDB6V4
U2	IO264NDB6V3
U3	IO264PDB6V3
U4	IO258PDB6V3
U5	IO258NDB6V3
U6	IO257PPB6V2
U7	IO261PPB6V3
U8	IO265NDB6V3
U9	IO263NDB6V3
U10	VCCIB6
U11	VCC
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND
U17	GND
U18	GND
U19	GND
U20	VCC
U21	VCCIB3
U22	IO120PDB3V0
U23	IO128PDB3V1
U24	IO124PDB3V1
U25	IO124NDB3V1
U26	IO126PDB3V1
U27	IO129PDB3V1
U28	IO127PDB3V1
U29	IO125PDB3V1
U30	IO121NDB3V0
V1	IO268NDB6V4
V2	IO262PDB6V3
V3	IO260PDB6V3
V4	IO252PDB6V2
V5	IO257NPB6V2
V6	IO261NPB6V3
V7	IO255PDB6V2
V8	IO259PDB6V3
V9	IO259NDB6V3
V10	VCCIB6
V11	VCC
V12	GND
V13	GND
V14	GND
V15	GND
V16	GND
V17	GND
V18	GND
V19	GND
V20	VCC
V21	VCCIB3
V22	IO120NDB3V0
V23	IO128NDB3V1
V24	IO132PDB3V2
V25	IO130PPB3V2
V26	IO126NDB3V1
V27	IO129NDB3V1
V28	IO127NDB3V1
V29	IO125NDB3V1
V30	IO123PDB3V1
W1	IO266NDB6V4
W2	IO262NDB6V3
W3	IO260NDB6V3
W4	IO252NDB6V2
W5	IO251NDB6V2
W6	IO251PDB6V2
W7	IO255NDB6V2
W8	IO249PPB6V1
W9	IO253PDB6V2
W10	VCCIB6
W11	VCC
W12	GND
W13	GND
W14	GND
W15	GND
W16	GND
W17	GND
W18	GND
W19	GND
W20	VCC
W21	VCCIB3
W22	IO134PDB3V2
W23	IO138PDB3V3
W24	IO132NDB3V2
W25	IO136NPB3V2
W26	IO130NPB3V2
W27	IO141PDB3V3
W28	IO135PDB3V2

Revision	Changes	Page
Advance v0.5 (continued)	The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50
	The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51
	The "Programming" section was updated to include information concerning serialization.	2-53
	The "JTAG 1532" section was updated to include SAMPLE/PRELOAD information.	2-54
	The "DC and Switching Characteristics" chapter was updated with new information.	Starting on page 3-1
	Table 3-6 was updated.	3-5
	In Table 3-10, PAC4 was updated.	3-8
	Table 3-19 was updated.	3-20
	The note in Table 3-24 was updated.	3-23
	All Timing Characteristics tables were updated from LVTTL to Register Delays	3-26 to 3-64
	The Timing Characteristics for RAM4K9, RAM512X18, and FIFO were updated.	3-74 to 3-79
	F_{TCKMAX} was updated in Table 3-98.	3-80
Advance v0.4 (October 2005)	The "Packaging Tables" table was updated.	ii
Advance v0.3	Figure 2-11 was updated.	2-9
	The "Clock Resources (VersaNets)" section was updated.	2-9
	The "VersaNet Global Networks and Spine Access" section was updated.	2-9
	The "PLL Macro" section was updated.	2-15
	Figure 2-27 was updated.	2-28
	Figure 2-20 was updated.	2-19
	Table 2-5 was updated.	2-25
	Table 2-6 was updated.	2-25
	The "FIFO Flag Usage Considerations" section was updated.	2-27
	Table 2-33 was updated.	2-51
	Figure 2-24 was updated.	2-31
	The "Cold-Sparing Support" section is new.	2-34
	Table 2-45 was updated.	2-64
	Table 2-48 was updated.	2-81
	Pin descriptions in the "JTAG Pins" section were updated.	2-51
	The "Pin Descriptions" section was updated.	2-50
	Table 3-7 was updated.	3-6